



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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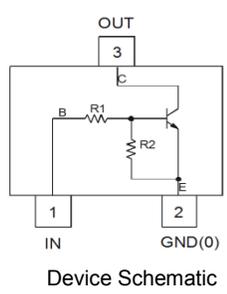
### Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Surface Mount Package Suited for Automated Assembly

### Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208  $\text{Ⓢ3}$
- Weight: 0.006 grams (Approximate)

Part Number	R1(NOM)	R2(NOM)
NK-DDTD113EU	1k $\Omega$	10k $\Omega$
NK-DDTD123EU	2.2k $\Omega$	2.2k $\Omega$
NK-DDTD143EU	4.7k $\Omega$	4.7k $\Omega$
NK-DDTD114EU	10k $\Omega$	10k $\Omega$
NK-DDTD122JU	0.22k $\Omega$	4.7k $\Omega$
NK-DDTD113ZU	1k $\Omega$	10k $\Omega$
NK-DDTD123YU	2.2k $\Omega$	10k $\Omega$
NK-DDTD133HU	3.3k $\Omega$	10k $\Omega$
NK-DDTD123TU	2.2k $\Omega$	Open
NK-DDTD143TU	4.7k $\Omega$	Open
NK-DDTD114TU	10k $\Omega$	Open
NK-DDTD114GU	0	10k $\Omega$



**Absolute Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage, (3) to (2)		$V_{CC}$	50	V
Input Voltage, (1) to (2)	NK-DDTD113EU	$V_{IN}$	-10 to +10	V
	NK-DDTD123EU		-10 to +12	
	NK-DDTD143EU		-10 to +30	
	NK-DDTD114EU		-10 to +40	
	NK-DDTD122JU		-5 to +5	
	NK-DDTD113ZU		-5 to +10	
	NK-DDTD123YU		-5 to +12	
Input Voltage, (2) to (1)	NK-DDTD133HU	$V_{EBO (MAX)}$	-6 to +20	V
	NK-DDTD123TU		5	
	NK-DDTD143TU			
Output Current		$I_C$	500	mA

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_D$	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

Note: 5. Mounted on FR4 PC Board with minimum recommended pad layout.

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

**R1, R2 Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	NK-DDTD113EU NK-DDTD123EU NK-DDTD143EU NK-DDTD114EU NK-DDTD122JU NK-DDTD113ZU NK-DDTD123YU NK-DDTD133HU	$V_{I(off)}$	0.5 0.5 0.5 0.5 0.5 0.3 0.3 0.3	—	—	V	$V_{CC} = 5V, I_O = 100\mu A$
	NK-DDTD113EU NK-DDTD123EU NK-DDTD143EU NK-DDTD114EU NK-DDTD122JU NK-DDTD113ZU NK-DDTD123YU NK-DDTD133HU	$V_{I(on)}$	—	—	3.0 3.0 3.0 3.0 3.0 2.0 2.0 2.0	V	$V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 10mA$ $V_O = 0.3V, I_O = 30mA$ $V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$
Output Voltage		$V_{O(on)}$	—	—	0.3V	V	$I_O/I_I = 50mA/2.5mA$
Input Current	NK-DDTD113EU NK-DDTD123EU NK-DDTD143EU NK-DDTD114EU NK-DDTD122JU NK-DDTD113ZU NK-DDTD123YU NK-DDTD133HU	$I_I$	—	—	7.2 3.8 1.8 0.88 28 7.2 3.6 2.4	mA	$V_I = 5V$
Output Current		$I_{O(off)}$	—	—	0.5	$\mu A$	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	NK-DDTD113EU NK-DDTD123EU NK-DDTD143EU NK-DDTD114EU NK-DDTD122JU NK-DDTD113ZU NK-DDTD123YU NK-DDTD133HU	$G_I$	33 39 47 56 47 56 56 56	—	—	—	$V_O = 5V, I_O = 50mA$
Gain-Bandwidth Product (Note 6)		$f_T$	—	200	—	MHz	$V_{CE} = 10V, I_E = 5mA, f = 100MHz$

**Electrical Characteristics** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

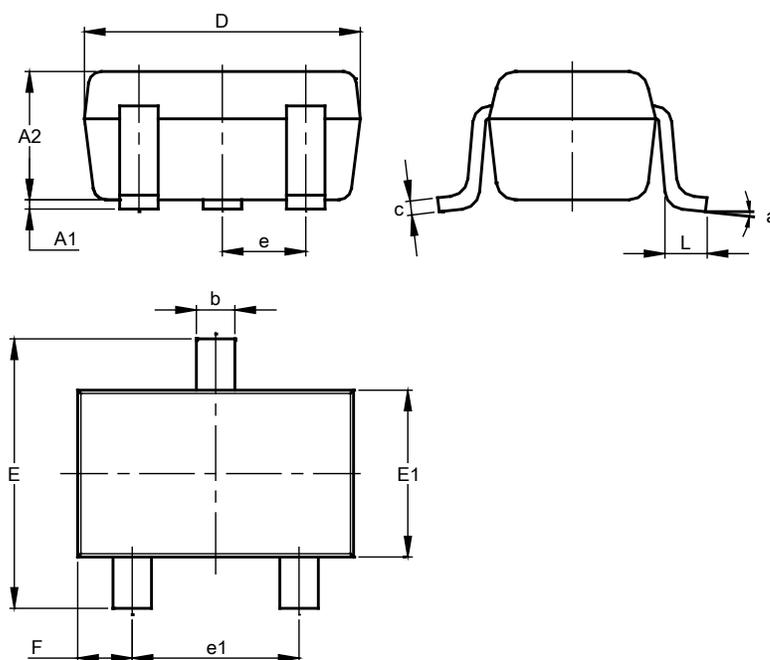
**R1-Only, R2-Only Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		$BV_{CBO}$	50	—	—	V	$I_C = 50\mu A$
Collector-Emitter Breakdown Voltage		$BV_{CEO}$	40	—	—	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	NK-DDTD123TU NK-DDTD143TU NK-DDTD114TU NK-DDTD114GU	$BV_{EBO}$	5	—	—	V	$I_E = 50\mu A$ $I_E = 50\mu A$ $I_E = 50\mu A$ $I_E = 720\mu A$
Collector Cutoff Current		$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 50V$
Emitter Cutoff Current	NK-DDTD123TU NK-DDTD143TU NK-DDTD114TU NK-DDTD114GU	$I_{EBO}$	— — — 300	—	0.5 0.5 0.5 580	$\mu A$	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	—	—	0.3	V	$I_C = 50mA, I_B = 2.5mA$
DC Current Transfer Ratio	NK-DDTD123TU NK-DDTD143TU NK-DDTD114TU NK-DDTD114GU	$h_{FE}$	100 100 100 56	250 250 250 —	600 600 600 —	—	$I_C = 5mA, V_{CE} = 5V$
Gain-Bandwidth Product (Note 6)		$f_T$	—	200	—	MHz	$V_{CE} = 10V, I_E = 5mA, f = 100MHz$

Note: 6. Transistor - for reference only

## Package Outline Dimensions

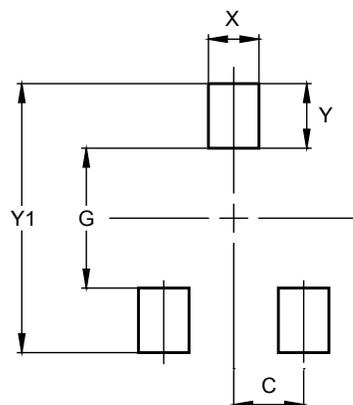
SOT323



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500